

| | Type | L # | Hits | Search Text | DBs | Comments |
|----|------|-----|--------|--|--|----------|
| 1 | BRS | L1 | 348945 | 257/\$.ccls. 438/\$.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| 2 | BRS | L2 | 102839 | 1 and (FET? or MISFET or MOSFET or transistor) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| 3 | BRS | L3 | 330 | 2 and (first and second) near (gate near dielectric) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| 4 | BRS | L4 | 4 | 3 and (SiO or (silicon near oxide)) and (TiO? or ((titanium or hafnium) near dioxide)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| 5 | BRS | L5 | 771 | 1 and (dual or double or (thick and thin)) near (gate near (oxide or dielectric)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| 6 | BRS | L6 | 46 | 5 and (first and second) near (gate near dielectric) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| 7 | BRS | L7 | 1047 | (furukawa-ryoichi or sakai-satoshi or yamamoto-satoshi).in. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| 8 | BRS | L8 | 0 | 7 and (first and second) near (gate near dielectric) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| 9 | BRS | L9 | 18 | 7 and MISFET | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| 10 | BRS | L10 | 173 | (dual or double or (thick and thin)) near (gate near (oxide or dielectric)).ti. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| 11 | BRS | L11 | 15 | 10 and (first and second) near (gate near dielectric) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| 12 | BRS | L12 | 6 | 11 and (dielectric near constant) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| 13 | BRS | L13 | 1195 | (dual or double or (thick and thin)) near (gate near (oxide or dielectric)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| 14 | BRS | L14 | 5 | 13 and (SiO or (silicon near oxide)) and (TiO? or ((titanium or hafnium) near dioxide)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |

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| 15 | BRS | L15 | 50 | 13 and (first and second) near (gate near dielectric) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| 16 | BRS | L16 | 9 | 15 and (different or lower or higher) near (dielectric near constant) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |